

A VARIATION IN THE LIFETIME OF MINOR
CURRENT CARRIERS IN THE PROCESSES
OF IRRADIATION AND ISOCHRONOUS
ANNEALING IN CRYSTALS *p*-Si

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S u m m a r y

Samples of *p*-type silicon irradiated with 8 MeV energy electrons have been studied. The comparison of the specific resistivity and lifetime of minor carriers τ under isochronous annealing testifies to that divacancies and V_3 -centers are recombination-active up to $T_{\text{ann}} = 300$ °C and enables us to assume that, after annealing at 400 – 500 °C, $(V_3 + O_2)$ and $(V_3 + O_3)$ complexes are responsible for alternation of τ , while $V_4, (V + B), (V_3 + O)$ and $(V_3 + O_2)$ are not recombination-active.